

## N-Channel Super Junction Power MOSFET III

### General Description

The series of devices use advanced trench gate super junction technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

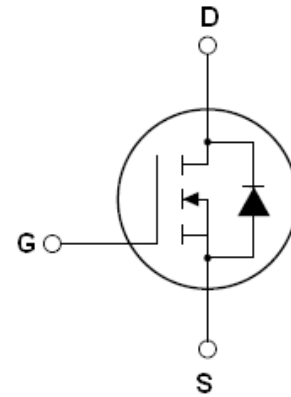
### Features

- New technology for high voltage device
- Low on-resistance and low conduction losses
- Small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested
- ROHS compliant

### Application

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)

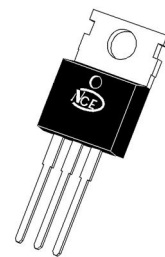
|                  |     |    |
|------------------|-----|----|
| $V_{DS}$         | 800 | V  |
| $R_{DS(ON) MAX}$ | 420 | mΩ |
| $I_D$            | 11  | A  |



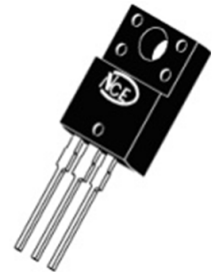
Schematic diagram

### Package Marking And Ordering Information

| Device     | Device Package | Marking    |
|------------|----------------|------------|
| NCE80T420  | TO-220         | NCE80T420  |
| NCE80T420F | TO-220F        | NCE80T420F |



TO-220



TO-220F

Table 1. Absolute Maximum Ratings ( $T_C=25^\circ\text{C}$ )

| Parameter  | Symbol          | NCE80T420 | NCE80T420F | Unit                |
|--|-----------------|-----------|------------|---------------------|
| Drain-Source Voltage ( $V_{GS}=0V$ )                                 | $V_{DS}$        | 800       |            | V                   |
| Gate-Source Voltage ( $V_{DS}=0V$ ), AC ( $f>1\text{ Hz}$ )          | $V_{GS}$        | $\pm 30$  |            | V                   |
| Continuous Drain Current at $T_C=25^\circ\text{C}$                   | $I_{D(DC)}$     | 11        | 11*        | A                   |
| Continuous Drain Current at $T_C=100^\circ\text{C}$                  | $I_{D(DC)}$     | 8.5       | 8.5*       | A                   |
| Pulsed drain current (Note 1)  | $I_{DM(pluse)}$ | 44        | 44*        | A                   |
| Maximum Power Dissipation( $T_C=25^\circ\text{C}$ )                  | $P_D$           | 188       | 33.8       | W                   |
| Derate above $25^\circ\text{C}$                                      |                 | 1.5       | 0.27       | W/ $^\circ\text{C}$ |
| Single pulse avalanche energy (Note 2)                               | $E_{AS}$        | 144       |            | mJ                  |
| Avalanche current (Note 1)   | $I_{AR}$        | 6         |            | A                   |
| Repetitive Avalanche energy, $t_{AR}$ limited by $T_{Jmax}$ (Note 1) | $E_{AR}$        | 0.7       |            | mJ                  |

| Parameter   | Symbol         | NCE80T420  | NCE80T420F | Unit |
|---|----------------|------------|------------|------|
| Drain Source voltage slope, $V_{DS} \leq 480V$ ,      | dv/dt          | 50         |            | V/ns |
| Reverse diode dv/dt, $V_{DS} \leq 480V, I_{SD} < I_D$ | dv/dt          | 15         |            | V/ns |
| Operating Junction and Storage Temperature Range      | $T_J, T_{STG}$ | -55...+150 |            | °C   |

\* limited by maximum junction temperature

**Table 2. Thermal Characteristic**

| Parameter   | Symbol     | NCE80T420 | NCE80T420F | Unit |
|---|------------|-----------|------------|------|
| Thermal Resistance, Junction-to-Case (Maximum)    | $R_{thJC}$ | 0.66      | 3.69       | °C/W |
| Thermal Resistance, Junction-to-Ambient (Maximum) | $R_{thJA}$ | 62.5      | 80         | °C/W |

**Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)**

| Parameter  | Symbol       | Condition   | Min | Typ  | Max       | Unit       |
|--|--------------|---|-----|------|-----------|------------|
| <b>On/off states</b>                                 |              |   |     |      |           |            |
| Drain-Source Breakdown Voltage                       | $BV_{DSS}$   | $V_{GS}=0V, I_D=250\mu A$                             | 800 |      |           | V          |
| Zero Gate Voltage Drain Current( $T_C=25^\circ C$ )  | $I_{DSS}$    | $V_{DS}=800V, V_{GS}=0V$                              |     | 0.05 | 1         | $\mu A$    |
| Zero Gate Voltage Drain Current( $T_C=125^\circ C$ ) | $I_{DSS}$    | $V_{DS}=800V, V_{GS}=0V$                              |     |      | 100       | $\mu A$    |
| Gate-Body Leakage Current                            | $I_{GSS}$    | $V_{GS}=\pm 20V, V_{DS}=0V$                           |     |      | $\pm 100$ | nA         |
| Gate Threshold Voltage                               | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=250\mu A$                         | 3   | 3.5  | 4         | V          |
| Drain-Source On-State Resistance                     | $R_{DS(ON)}$ | $V_{GS}=10V, I_D=5.5A$                                |     | 350  | 420       | m $\Omega$ |
| <b>Dynamic Characteristics</b>                       |              |   |     |      |           |            |
| Forward Transconductance                             | $g_{FS}$     | $V_{DS} = 20V, I_D = 5.5A$                            |     | 7    |           | S          |
| Input Capacitance                                    | $C_{ISS}$    | $V_{DS}=50V, V_{GS}=0V,$<br>$F=1.0MHz$                |     | 2600 |           | PF         |
| Output Capacitance                                   | $C_{OSS}$    |   |     | 95   |           | PF         |
| Reverse Transfer Capacitance                         | $C_{RSS}$    |   |     | 7    |           | PF         |
| Total Gate Charge                                    | $Q_g$        | $V_{DS}=640V, I_D=11A,$<br>$V_{GS}=10V$               |     | 48   |           | nC         |
| Gate-Source Charge                                   | $Q_{gs}$     |   |     | 17   |           | nC         |
| Gate-Drain Charge                                    | $Q_{gd}$     |   |     | 14   |           | nC         |
| <b>Switching times</b>                               |              |   |     |      |           |            |
| Turn-on Delay Time                                   | $t_{d(on)}$  | $V_{DD}=480V, I_D=5.5A,$<br>$R_G=4\Omega, V_{GS}=10V$ |     | 12   |           | nS         |
| Turn-on Rise Time                                    | $t_r$        |   |     | 7    |           | nS         |
| Turn-Off Delay Time                                  | $t_{d(off)}$ |   |     | 62   |           | nS         |
| Turn-Off Fall Time                                   | $t_f$        |   |     | 5    |           | nS         |
| <b>Source- Drain Diode Characteristics</b>           |              |   |     |      |           |            |
| Source-drain current(Body Diode)                     | $I_{SD}$     | $T_C=25^\circ C$                                      |     |      | 11        | A          |
| Pulsed Source-drain current(Body Diode)              | $I_{SDM}$    |   |     |      | 44        | A          |
| Forward on voltage                                   | $V_{SD}$     | $T_J=25^\circ C, I_{SD}=11A, V_{GS}=0V$               |     | 0.9  | 1.3       | V          |
| Reverse Recovery Time                                | $t_{rr}$     | $T_J=25^\circ C, I_F=11A, di/dt=100A/\mu s$           |     | 290  |           | nS         |
| Reverse Recovery Charge                              | $Q_{rr}$     |   |     | 2.2  |           | $\mu C$    |
| Peak Reverse Recovery Current                        | $I_{rrm}$    |   |     | 15   |           | A          |

**Notes** 1. Repetitive Rating: Pulse width limited by maximum junction temperature

2.  $T_J=25^\circ C, V_{DD}=50V, V_G=10V, R_G=25\Omega$

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure1. Safe operating area for TO-220

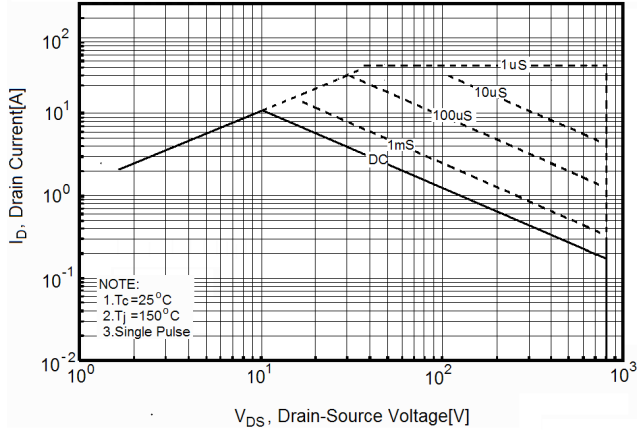


Figure2. Safe operating area for TO-220F

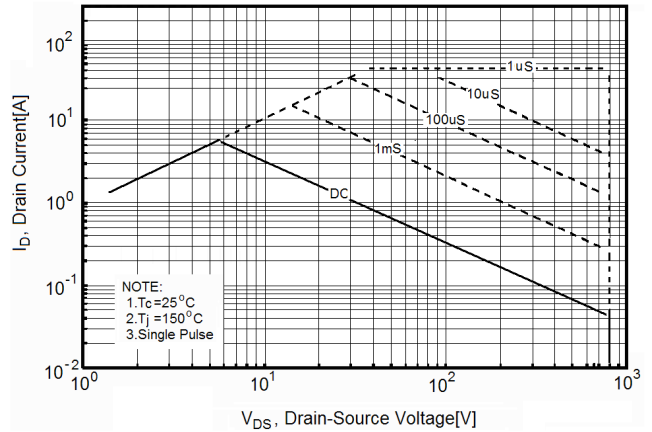


Figure3. Source-Drain Diode Forward Voltage

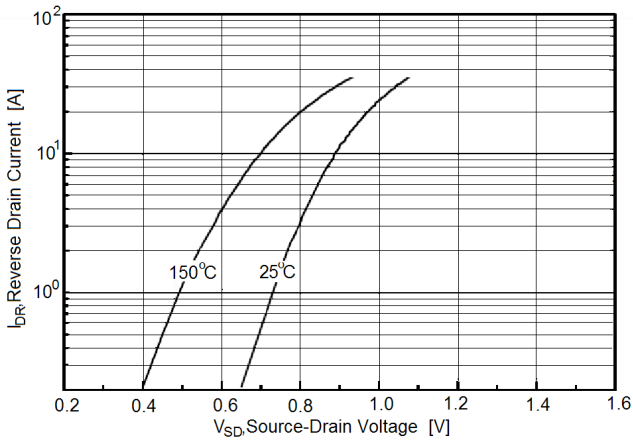


Figure4. Output characteristics

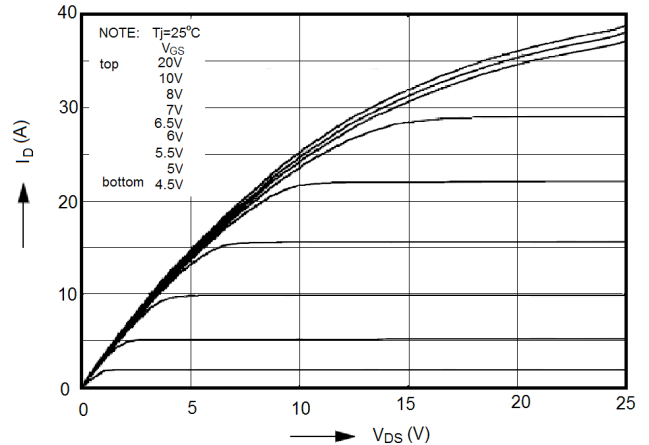


Figure5. Transfer characteristics

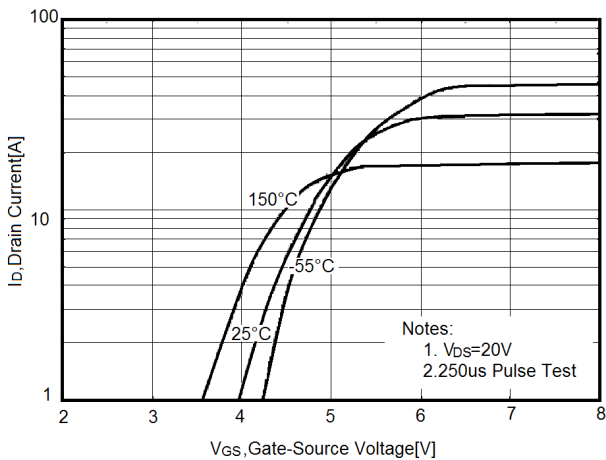
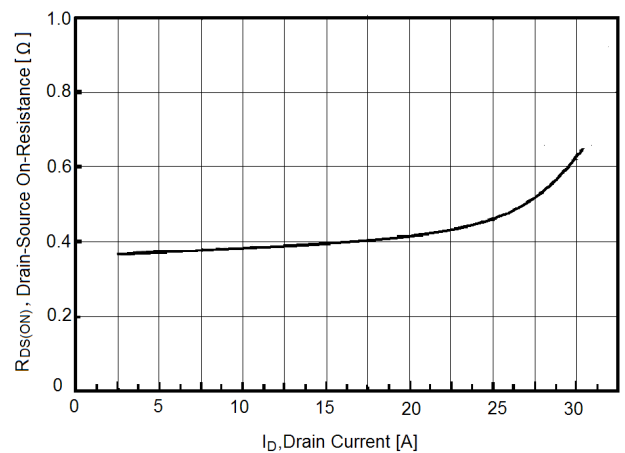
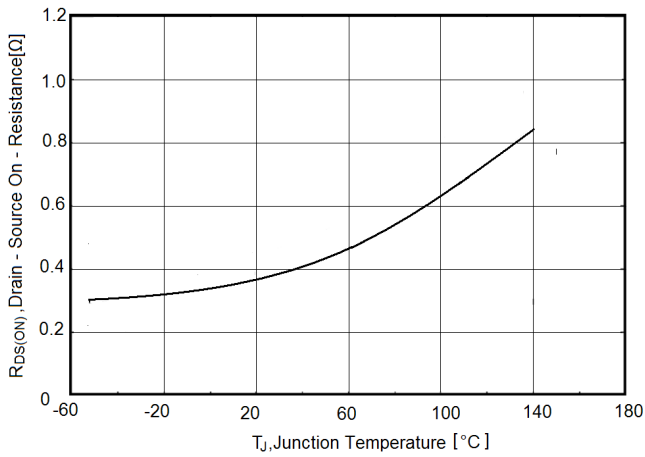


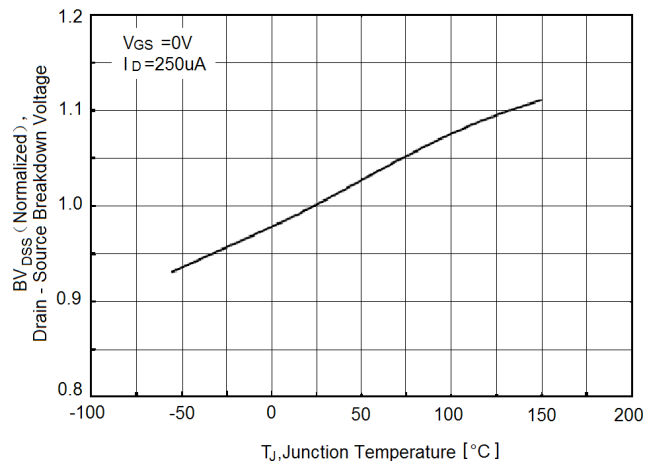
Figure6. Static drain-source on resistance



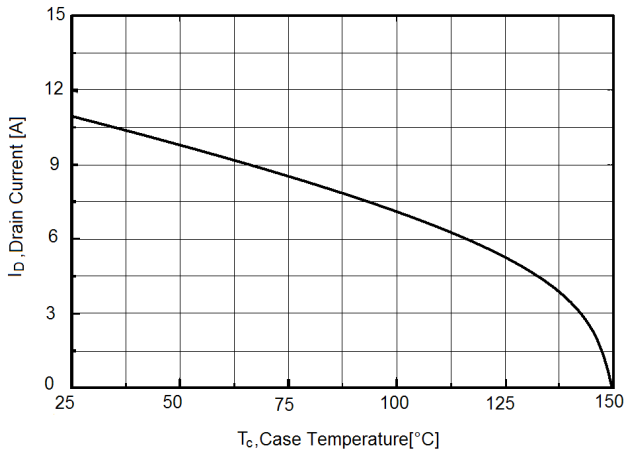
**Figure7.  $R_{DS(ON)}$  vs Junction Temperature**



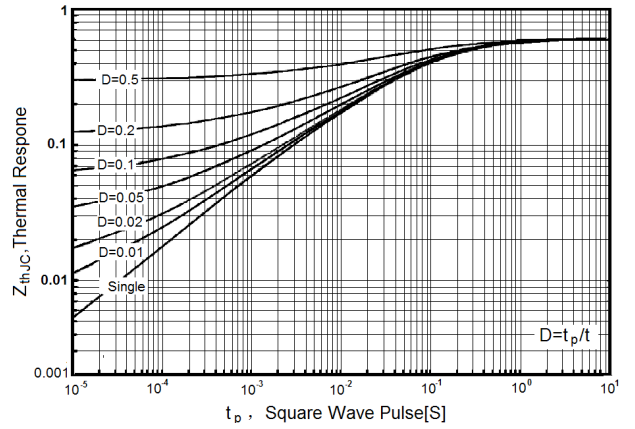
**Figure8.  $BV_{DSS}$  vs Junction Temperature**



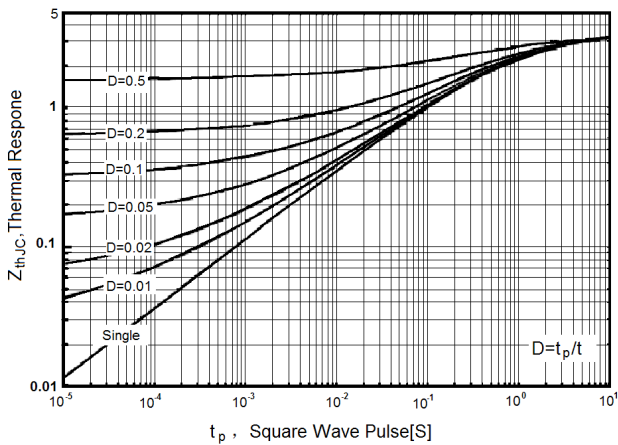
**Figure9. Maximum  $I_D$  vs Junction Temperature**



**Figure10. Transient Thermal Impedance for TO-220**

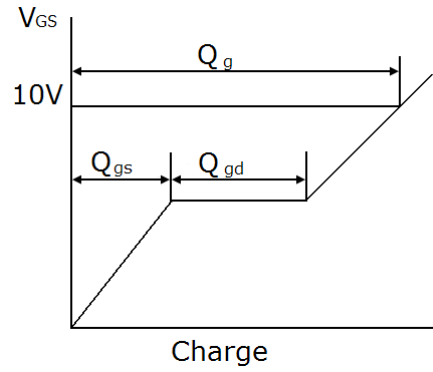
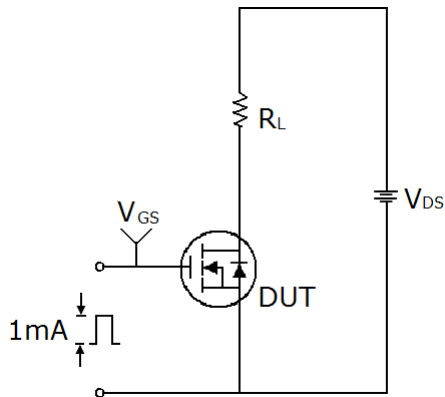


**Figure11. Transient Thermal Impedance for TO-220F**

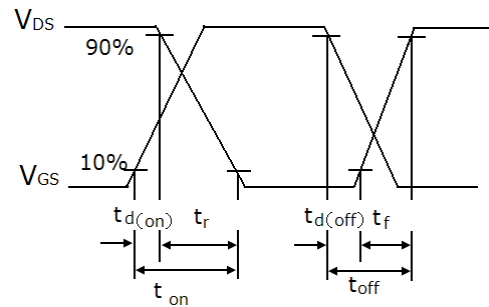
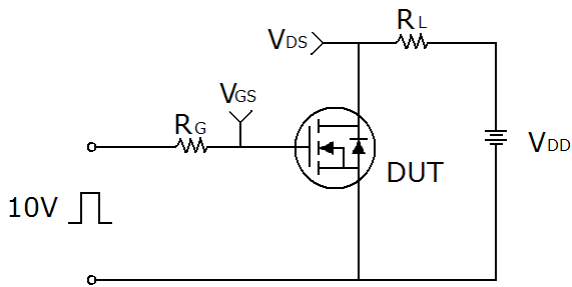


## Test circuit

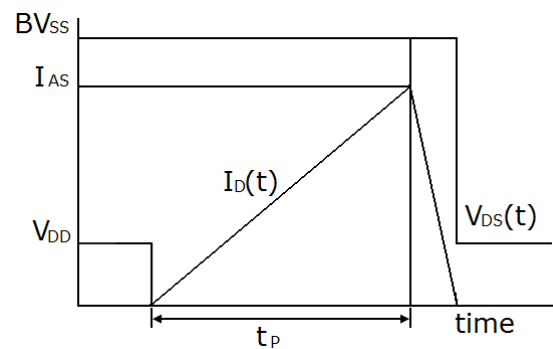
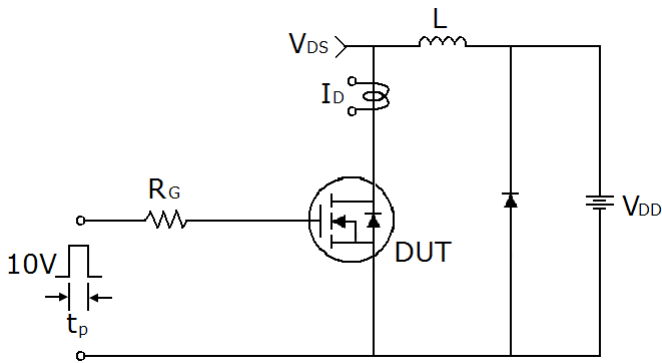
### 1) Gate charge test circuit & Waveform



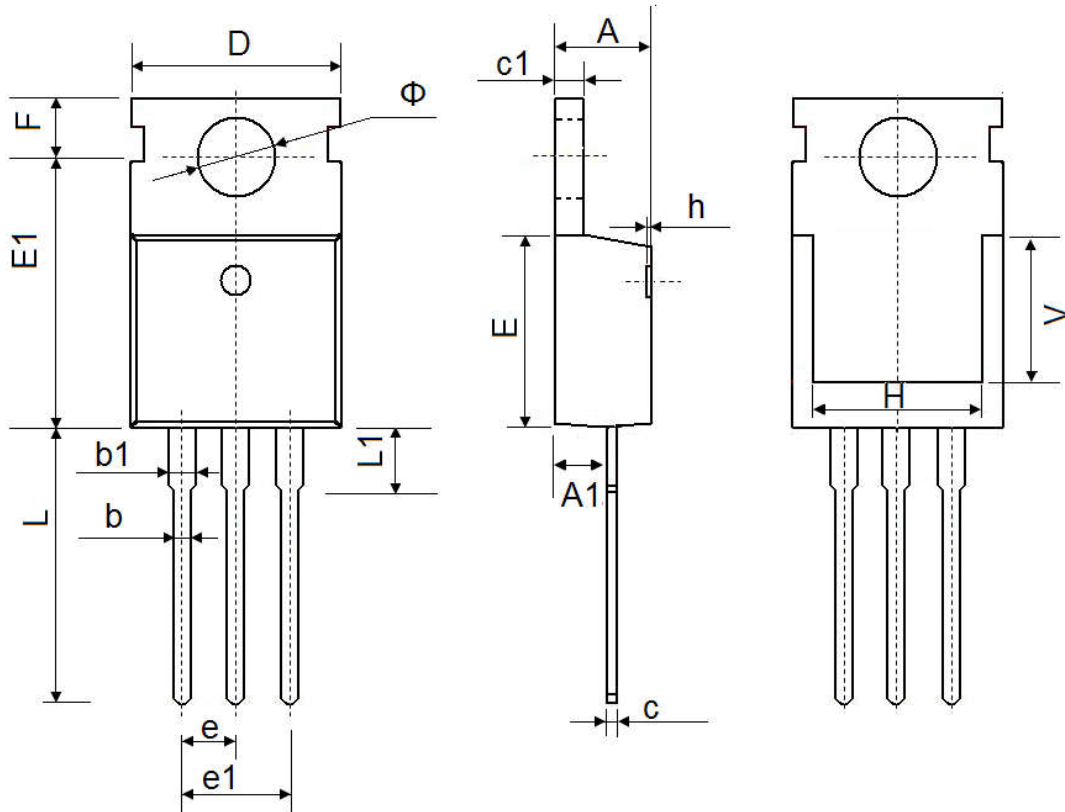
### 2) Switch Time Test Circuit:



### 3) Unclamped Inductive Switching Test Circuit & Waveforms

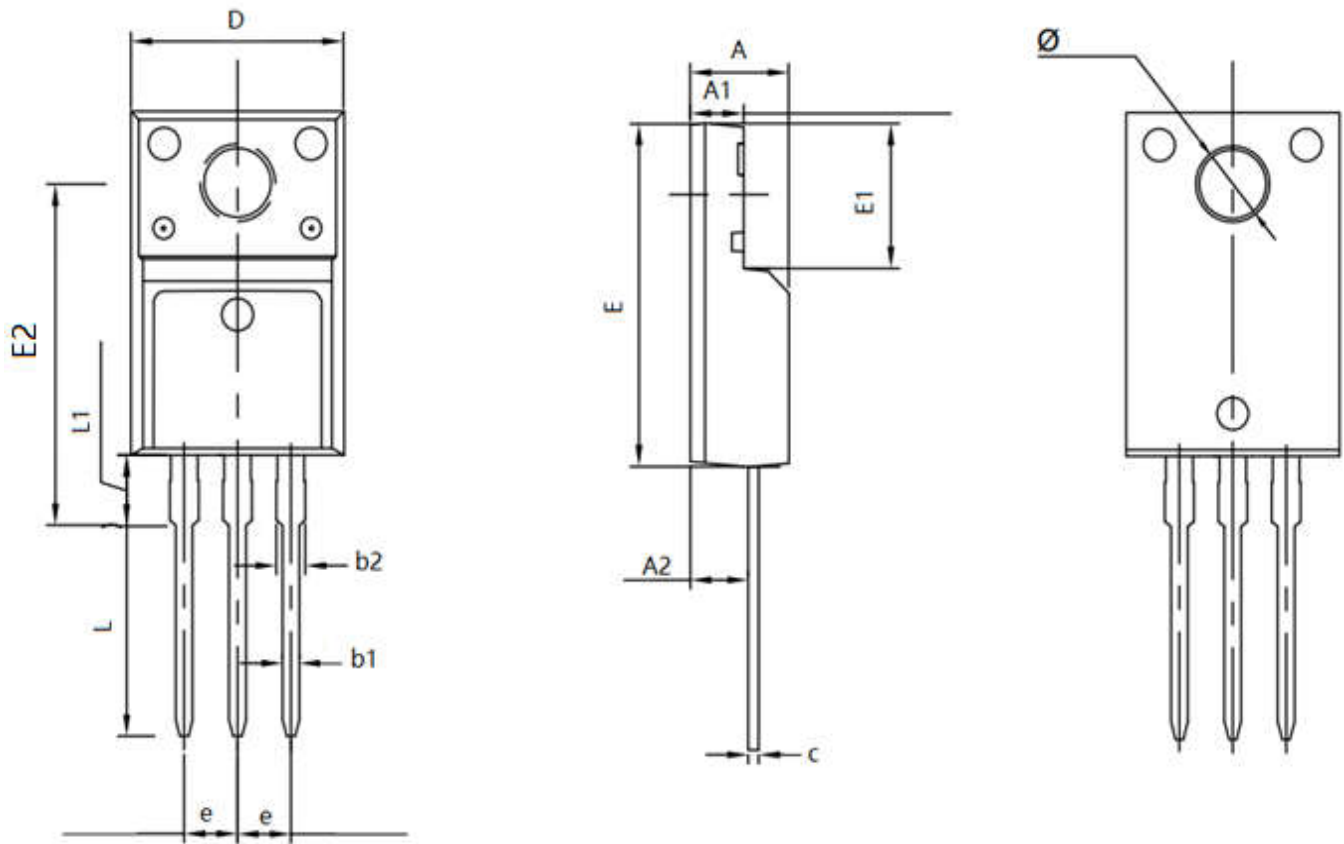


## TO-220-3L-C Package Information



| Symbol | Dimensions In Millimeters |        | Dimensions In Inches |       |
|--------|---------------------------|--------|----------------------|-------|
|        | Min.                      | Max.   | Min.                 | Max.  |
| A      | 4.400                     | 4.600  | 0.173                | 0.181 |
| A1     | 2.250                     | 2.550  | 0.089                | 0.100 |
| b      | 0.710                     | 0.910  | 0.028                | 0.036 |
| b1     | 1.170                     | 1.370  | 0.046                | 0.054 |
| c      | 0.330                     | 0.650  | 0.013                | 0.026 |
| c1     | 1.200                     | 1.400  | 0.047                | 0.055 |
| D      | 9.910                     | 10.250 | 0.390                | 0.404 |
| E      | 8.9500                    | 9.750  | 0.352                | 0.384 |
| E1     | 12.650                    | 12.950 | 0.498                | 0.510 |
| e      | 2.540 TYP.                |        | 0.100 TYP.           |       |
| e1     | 4.980                     | 5.180  | 0.196                | 0.204 |
| F      | 2.650                     | 2.950  | 0.104                | 0.116 |
| H      | 7.900                     | 8.100  | 0.311                | 0.319 |
| h      | 0.000                     | 0.300  | 0.000                | 0.012 |
| L      | 12.900                    | 13.400 | 0.508                | 0.528 |
| L1     | 2.850                     | 3.250  | 0.112                | 0.128 |
| V      | 7.500 REF.                |        | 0.295 REF.           |       |
| Φ      | 3.400                     | 3.800  | 0.134                | 0.150 |

## TO-220F Package Information



| Symbol | Dimensions In Millimeters |        | Dimensions In Inches |       |
|--------|---------------------------|--------|----------------------|-------|
|        | Min.                      | Max.   | Min.                 | Max.  |
| A      | 4.500                     | 4.900  | 0.177                | 0.193 |
| A1     | 2.340                     | 2.740  | 0.092                | 0.108 |
| A2     | 2.560                     | 2.960  | 0.101                | 0.117 |
| b1     | 0.700                     | 0.900  | 0.028                | 0.035 |
| b2     | 1.180                     | 1.580  | 0.046                | 0.062 |
| c      | 0.400                     | 0.600  | 0.016                | 0.024 |
| D      | 9.960                     | 10.360 | 0.392                | 0.408 |
| E      | 15.670                    | 15.970 | 0.617                | 0.629 |
| E1     | 6.500                     | 6.900  | 0.256                | 0.272 |
| E2     | 15.500                    | 16.100 | 0.610                | 0.634 |
| e      | 2.540 TYP                 |        | 0.100 TYP            |       |
| φ      | 3.080                     | 3.280  | 0.121                | 0.129 |
| L      | 12.640                    | 13.240 | 0.498                | 0.521 |
| L1     | 3.030                     | 3.430  | 0.119                | 0.135 |

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